PROCESS CP753V

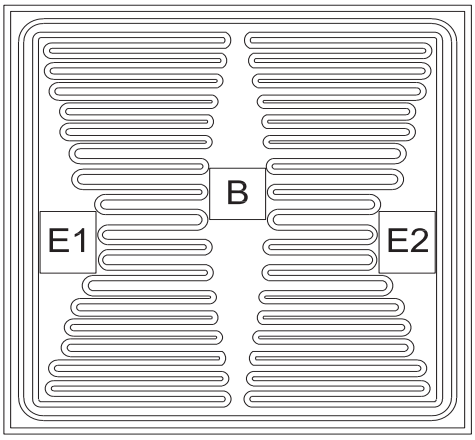
Small Signal Transistors

PNP - High Current Transistor Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	66 x 66 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	7.9 x 7.9 MILS
Emitter 1 Bonding Pad Area	7.9 x 9.5 MILS
Emitter 2 Bonding Pad Area	7.9 x 9.5 MILS
Top Side Metalization	Al-Si - 30,000Å
Back Side Metalization	Ti/Ni/Ag - 2,000Å/3,000Å/20,000Å

GEOMETRY



BACKSIDE: COLLECTOR R0

GROSS DIE PER 5 INCH WAFER

3,878

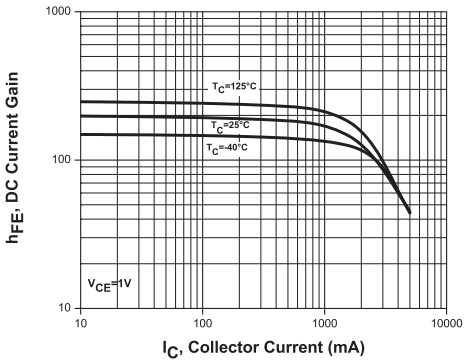
PRINCIPAL DEVICE TYPES

CZT953

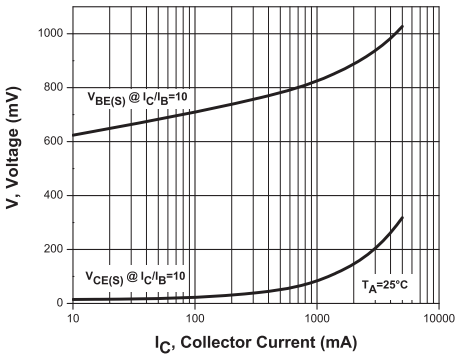
PROCESS CP753V

Typical Electrical Characteristics

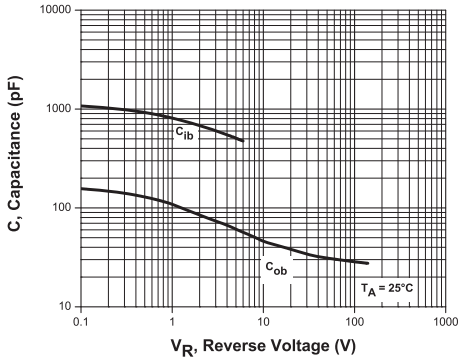
DC Current Gain



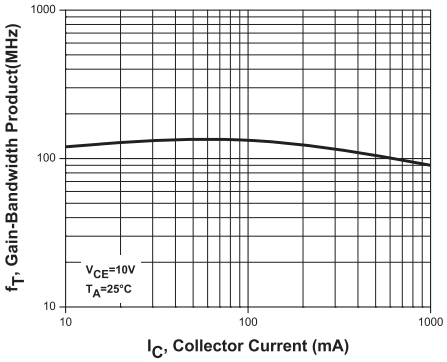
"ON" Voltage



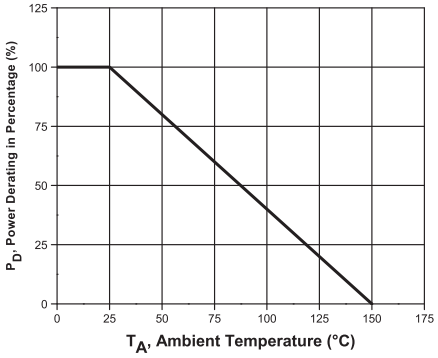
Capacitance



Current Gain-Bandwidth Product



Normalized Power Derating



R2 (22-March 2010)